

Product Specification

XBLW AO4805

P-Channel Enhancement Mode MOSFET











Description

The AO4805 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

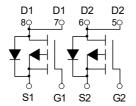
General Features

- \rightarrow VDS = -30V, ID = -8.5A
- > RDS(ON) < 18m @ V GS=-10V
- > RDS(ON) < 28m @ V GS=-4.5V

Application

- > PWM application
- Load switch





Dual P-Channel MOSFET

Package Marking and Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW AO4805	SOP-8	AO4805	Tape	3000Pcs/Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-30	V
V _G s	Gate-Source Voltage	±20	V
l _D	Drain Current-Continuous	-8.5	А
Ірм	Drain Current-Pulsed (Note 1)	-26	А
P _D	Maximum Power Dissipation	1.5	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	85	°C/W



Electrical Characteristics (TJ=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0 V , I_D =-250 u A	-30			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.022		V/°C	
D	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-6A		14	18	m0	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-4A		22	28	mΩ	
V _{GS(th)}	Gate Threshold Voltage	VV I 2500A	-1.0		-2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	─_V _{GS} =V _{DS} , I _D =-250uA		4.6		mV/°C	
1	Drain Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	uA	
IDSS	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55°C			-5	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V_{DS} =-5 V , I_{D} =-6 A		17		S	
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13		Ω	
Qg	Total Gate Charge (-4.5V)			12.6			
Q_{gs}	Gate-Source Charge	V_{DS} =-15V , V_{GS} =-4.5V , I_{D} =-6A		4.8		nC	
Q_{gd}	Gate-Drain Charge			4.8			
T _{d(on)}	Turn-On Delay Time			4.6			
Tr	Rise Time	V_{DD} =-15 V , V_{GS} =-10 V , R_{G} =3.3 Ω ,		14.8		20	
$T_{d(off)}$	Turn-Off Delay Time	I _D =-6A		41		ns	
T _f	Fall Time			19.6			
Ciss	Input Capacitance			1345			
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		194		pF	
C _{rss}	Reverse Transfer Capacitance		-	158			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,5}	\/-=\/-=0\/			-6.5	Α
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			-26	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V
t _{rr}	Reverse Recovery Time			16.3		nS
Qrr	Reverse Recovery Charge	lF=-6A,dl/dt=100A/µs,Tյ=25°C		5.9		nC

Note

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$

4.The power dissipation is limited by 150°C junction temperature

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.1mH,I_{AS}=-38A

^{5.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

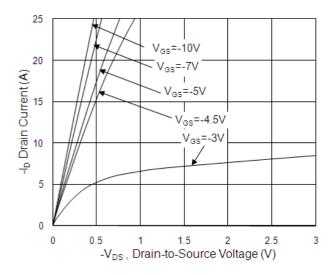


Fig.1 Typical Output Characteristics

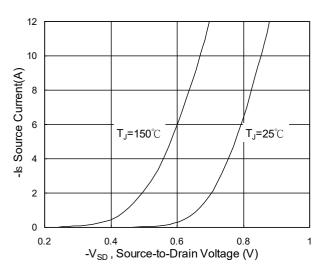


Fig.3 Forward Characteristics of Reverse

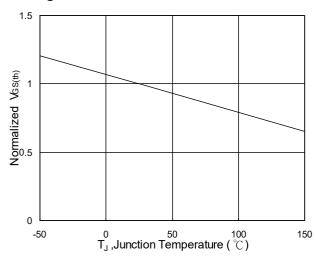


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

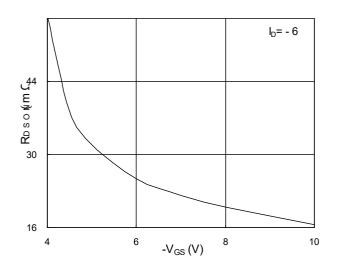


Fig.2 On-Resistance v.s Gate-Source

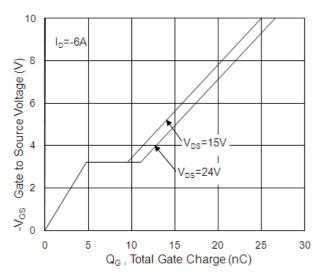


Fig.4 Gate-Charge Characteristics

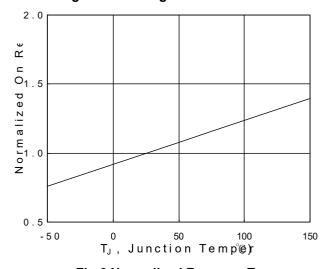
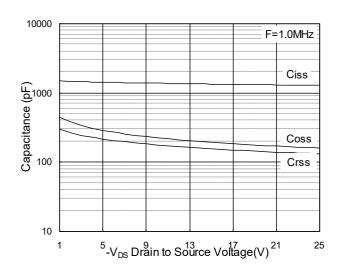


Fig.6 Normalized R_{DSON} vs. T_J



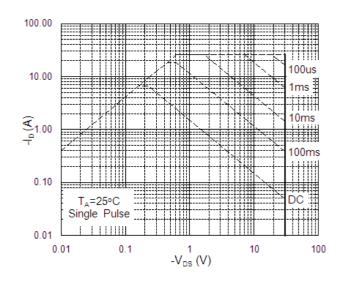


Fig.7 Capacitance

Fig.8 Safe Operating Area

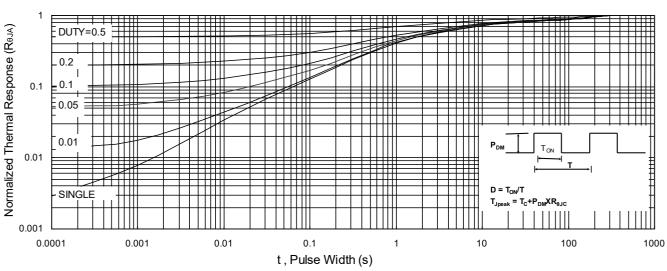


Fig.9 Normalized Maximum Transient Thermal Impedance

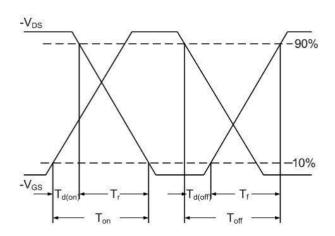


Fig.10 Switching Time Waveform

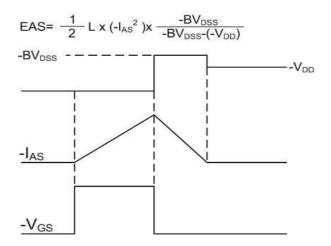
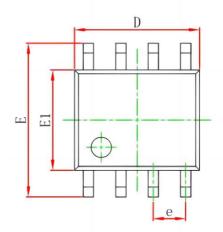


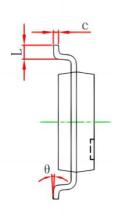
Fig.11 Unclamped Inductive Switching Waveform

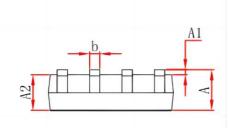


Package Outline Dimensions

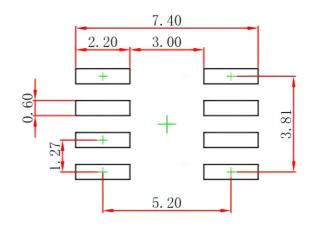
SOP-8







Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0. 510	0. 013	0.020
С	0.170	0. 250	0.007	0.010
D	4.800	5.000	0.189	0. 197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6. 200	0. 228	0. 244
E1	3.800	4.000	0.150	0. 157
L	0.400	1. 270	0.016	0.050
θ	0 °	8°	0 °	8°



Note:

- 1.Controlling dimension: In millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.



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